

Surface Mount Fast Switching Diodes

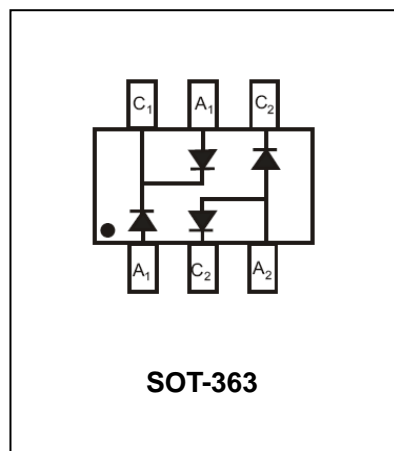
BAV756DW

FEATURES

- Fast switching speed.
- For general purpose switching application.
- High conductance.
- One BAV70 circuit and one BAW56 circuit in one package.
- Easily connected as full wave bridge.



Lead-free



APPLICATIONS

- For general purpose switching application.

ORDERING INFORMATION

Type No.	Marking	Package Code
BAV756DW	KCA	SOT-363

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Characteristic	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	100	V
V_R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Reverse Voltage	75	V
$V_{R(RMS)}$	RMS Reverse Voltage	53	V
I_O	Average Rectified Output Current	150	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current	@t=1.0us 2.0 @t=1.0s 1.0	A
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	625	°C/W
T_j, T_{stg}	Junction and Storage Temperature	-65 to +150	°C

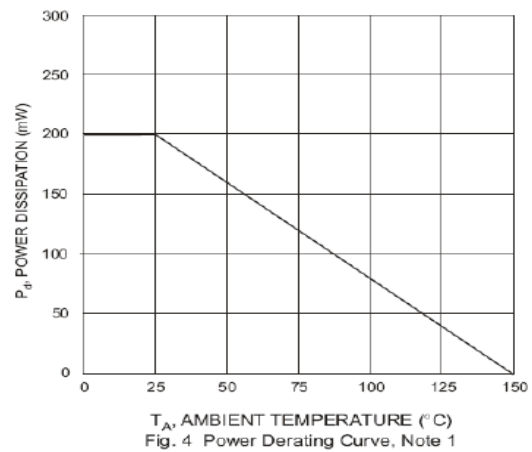
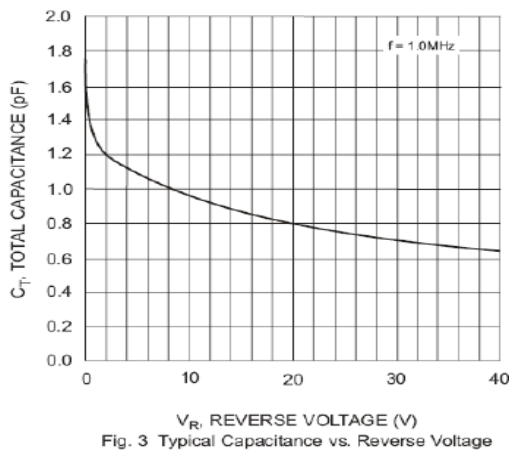
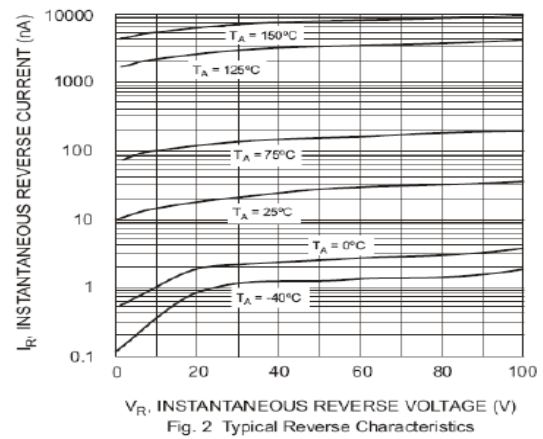
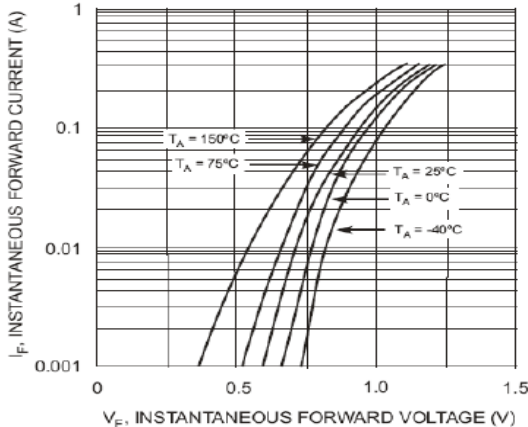
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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=2.5\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$		2.5	μA
		$V_R=75V, T_j=150^\circ C$		50	μA
		$V_R=25V, T_j=150^\circ C$		30	μA
		$V_R=20V$		25	nA
Forward voltage	V_F	$I_F=1.0mA$		0.715	V
		$I_F=10mA$		0.855	
		$I_F=50mA$		1.0	
		$I_F=150mA$		1.25	
Total Capacitance	C_T	$V_R=0V, f=1.0MHz$		2.0	pF
Reverse Recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1 \cdot I_R,$ $R_L=100\Omega$		4.0	ns

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



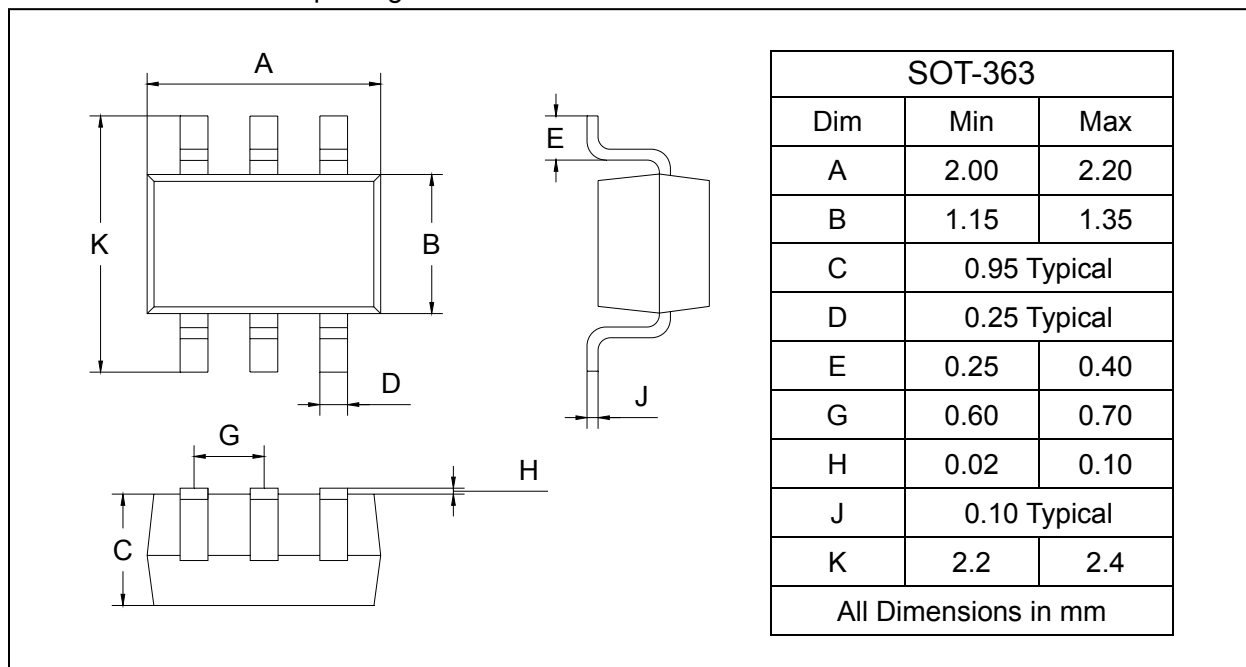
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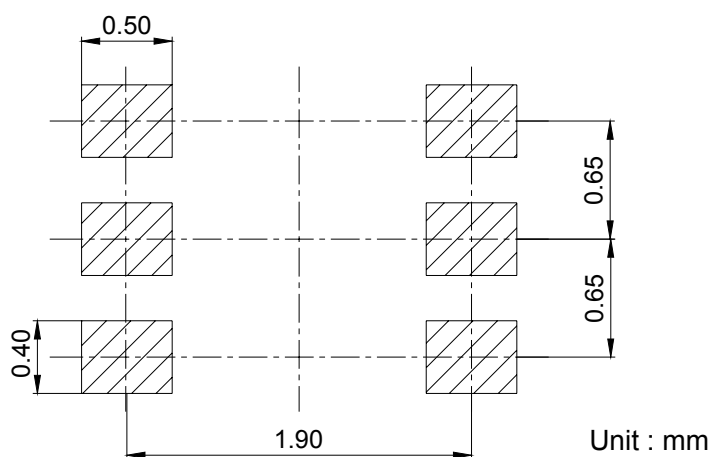
PACKAGE OUTLINE

Plastic surface mounted package

SOT-363



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAV756DW	SOT-363	3000/Tape&Reel